



Shantou Huashan Electronic Devices Co.,Ltd.

NPN SILICON TRANSISTOR

H1836

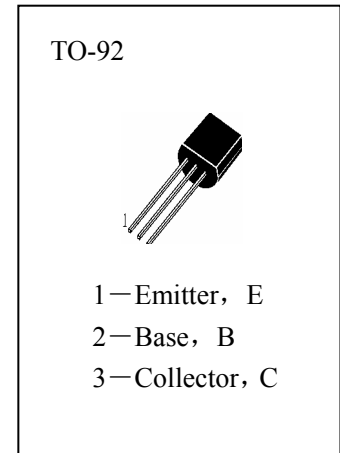
■ FOR HIGH VOLTAGE AMPLIFIER APPLICATIONS

PLASMA DISPLAY, NIXIE TUBE DRIVER APPLICATIONS.

COLOR TV VIDEO OUTPUT APPLICATIONS.

■ ABSOLUTE MAXIMUM RATINGS (T<sub>a</sub>=25°C)

T <sub>stg</sub>	Storage Temperature	-55~150°C
T <sub>j</sub>	Junction Temperature	150°C
P <sub>C</sub>	Collector Dissipation	625mW
V <sub>CB0</sub>	Collector-Base Voltage	300V
V <sub>CEO</sub>	Collector-Emitter Voltage	300V
V <sub>EBO</sub>	Emitter-Base Voltage	6V
I <sub>C</sub>	Collector Current	100mA



■ ELECTRICAL CHARACTERISTICS (T<sub>a</sub>=25°C)

Symbol	Characteristics	Min	Typ	Max	Unit	Test Conditions
BV <sub>CB0</sub>	Collector-Base Breakdown Voltage	300			V	I <sub>C</sub> =100 μ A, I <sub>E</sub> =0
BV <sub>CEO</sub>	Collector-Emitter Breakdown Voltage	300			V	I <sub>C</sub> =1mA, I <sub>B</sub> =0
I <sub>CBO</sub>	Collector Cut-off Current			0.1	μ A	V <sub>CB</sub> =300V, I <sub>E</sub> =0
I <sub>EBO</sub>	Emitter Cut-off Current			0.1	μ A	V <sub>EB</sub> =6V, I <sub>C</sub> =0
H <sub>FE</sub> (1)	DC Current Gain	20				V <sub>CE</sub> =10V, I <sub>C</sub> =1mA
H <sub>FE</sub> (1)		30		150		V <sub>CE</sub> =10V, I <sub>C</sub> =20mA
V <sub>CE(sat)</sub>	Collector- Emitter Saturation Voltage			0.5	V	I <sub>C</sub> =20mA, I <sub>B</sub> =2mA
V <sub>BE(sat)</sub>	Base-Emitter Saturation Voltage			1.2	V	I <sub>C</sub> =20mA, I <sub>B</sub> =2mA
f <sub>T</sub>	Current Gain-Bandwidth Product	50	80		MHz	V <sub>CE</sub> =10V, I <sub>C</sub> =20mA
C <sub>ob</sub>	Output Capacitance		3	4	pF	V <sub>CB</sub> =20V, I <sub>E</sub> =0, f=1MHz